E ects of pressure on di usion and vacancy form ation in M gO from non-empirical free-energy integrations.

Joel Ita and Ronald E.Cohen

Geophysical Laboratory and Center for H igh P ressure Research, Carnegie Institution of W ashington, 5251 B road B ranch Road, NW, W ashington, DC 20015-1305 (M arch 23, 2024)

The free energies of vacancy pair form ation and m igration in M gO were computed via m olecular dynam ics using free-energy integrations and a non-empirical ionic m odel with no adjustable param - eters. The intrinsic di usion constant for M gO was obtained at pressures from 0 to 140 G Pa and tem peratures from 1000 to 5000 K. Excellent agreem ent was found with the zero pressure di usion data within experim ental error. The hom ologous tem perature m odel which relates di usion to the m elting curve describes well our high pressure results within our theoretical fram ework.

61.72 Bb,62.50.+ p,66.30 D n,91.60 Ed,91.60 G f

D i usion and vacancy form ation are critical to kinetic processes in materials, yet little is known about di usion at ultra-high pressures due to experimental di culties. Rheology of oxide minerals at high pressures is also crucial in geophysics and is dependent on di usive behavior which is only available experimentally at relatively low pressures [1]. In ionic systems such as MgO, the dominant intrinsic defect is the pair vacancy [2{4] with Mg and O sites vacant. Previous work on vacancies in MgO used pseudopotential computations [5] or lattice dynamics or the Mott-Littleton approach with a variety of sem i-em pirical potentials [6,7]. The accuracy of quasiharm onic lattice dynamics calculations degrades above the D ebye tem perature and the Mott-Littleton procedure and pseudopotential com putations were restricted to 0 K.

W e used molecular dynam ics (M D) with non-empirical potentials to determ ine the self-di usion coe cient D where [2]

$$D = Z_f \frac{Z_m}{6} l^2 \exp\left(\frac{\frac{G_f}{W} + G_m}{k_b T}\right)$$
(1)

 Z_{f} is the num ber of equivalent ways of form ing a vacancy type, Z_{m} is the num ber of equivalent di usion paths, l is the jump distance, is the attempt frequency, G_{f} and G_{m} are the energies of form ation and m igration, respectively and W is the solubility factor for polyatom ic m aterials. If the sites are uncorrelated (Schottky defect), then, for rocksalt structured (B1) crystals such as M gO, W = 2, $Z_{f} = 1$, $Z_{m} = 12$. Highly correlated defects (bound pair) require W = 1 and $Z_{f} = 6$. Symmetry and energy considerations determ ine the value of Z_{m} . In either case, $l^{2} = a^{2}=2$ where a is the cubic cell parameter.

We used the variational induced breathing (V \mathbb{B}) m odel which reliably gives the therm all properties and equation of state of M gO [8] to compute the energetics and interatom ic forces. The V \mathbb{B} m odel is a G ordon-K im type m odel [9] in which the total charge density is

m odeled by overlapping ionic charge densities which are computed using the local density approximation (LDA) [10]. The total energy is a sum of three term s: (a) the long-range electrostatic energy computed using the Ewald method, (b) the self-energy of each atom and (c) the short range interaction energy, the sum of the kinetic, short-range electrostatic and exchange-correlation energies from the LDA. There are three approximations beyond the LDA [11]: (1) The charge density is modeled rather than computed self-consistently. Comparisons with accurate linearized augmented plane wave (LAPW) com putations show this is a good approxim ation for M gO [12]; (2) the pair approximation is used for the shortrange interactions (c) which is a good approximation as long as closed shell ions are used [13]; (3) the Thom as-Ferm i kinetic energy is used for the short-range overlap kinetic energy. The self-energy (b) includes the correct LDA Kohn-Sham kinetic energy. 0^2 is not stable in the free state and is stabilized by introducing a sphere of 2+ charge (W atson sphere) around it in the LDA atom ic calculations. Interactions are obtained for overlapping ion pairs at di erent distances with di erent W atson sphere radii on the O's. For e ciency, the interactions were t with a 21 parameter analytical expression as functions of r, the interatom ic distance, and $U_i = z_i = R_i$ where U_i ; z_i , and R_i are the W atson sphere potential, charge (2+) and radius for atom i, respectively. During the simulations, the total energy was variationally optim ized with respect to all of the W atson sphere radii at each tim e step.

The attempt frequency was determined by Fourier transforming the trajectories of the di using ion projected onto the shortest path to the vacancy. We considered two models: (1) the lowest frequency peak in the spectrum, assuming that the di usive motion is mostly from the lowest energy mode and (2) the average frequency computed from the Fourier transform. In the rst case we found that = 52 THz and is independent

of P and T over the range studied. The second case gave an attempt frequency that is within a factor 2 of the low frequency value. G iven the uncertainties in the calculations and experimental determinations, the dierence in the nal results between these two approaches is small and we adopted case (1) below.

Free energies were computed with the nite time variationalor \adiabatic switching" therm odynam ic integration m ethod [14]. The free energy di erence between the initial and nal state is

$$F = \int_{0}^{Z_{1}} \frac{\partial F()}{\partial d} = \int_{0}^{Z_{1}} h \frac{\partial H()}{\partial d} = d$$
(2)

where is a progress variable which ranges from 0 to 1 as the system \switches" from its initial to nal state, H is the system H am iltonian, and hi represents an ensemble average. In order to obtain $G_{\rm f}$, we rst calculated the free energy di erence between an ideal crystal at volume, $V_{\rm I}$, giving the desired average P at T and an E instein crystal at the same V and T. This was repeated for a defective crystal with a bound vacancy pair in each periodic cell at $V_{\rm D}$ corresponding to P. Then for an N atom periodic cell

$$G_{f} = F_{D}^{N-L} (V_{D}) \frac{N-L}{N} F_{I}^{N} (V_{I}) + P V_{D} \frac{N-L}{N} V_{I}$$
(3)

where $F_D^{N-L}(V_D)$ is the Helmholtz free energy of a defective crystal with L vacant sites and $F_I^N(V_I)$ is the Helmholtz free energy of the ideal crystal. The Ham iltonian took the form

$$H() = H_{VB}(1) + H_{ein}$$
 (4)

where H_{ein} is the H am iltonian for an E instein crystal [15] which can be written as

$$H_{ein} = K + U_{o} + \sum_{i=1}^{X^{i}} \frac{1}{2} m_{i}!_{ein;i} (x_{i} + x_{i0}^{i})^{2}$$
(5)

where K is the kinetic energy, U_{\circ} is the static contribution to the potential, m_i, x_i , x_{i0}^{\dagger} , and $!_{ein;i}$ are the mass, position, static lattice position, and E instein frequency of the ith particle, respectively. The form of as a function of the scaled time, , is

() =
5
 (70 4 315 3 + 540 2 420 + 126) (6)

where $= t=t_s$, t is the elapsed time, and t_s is the total switching time [15].

M igration free energies were calculated using the adiabatic switching procedure at constant P and T. We computed the energy it takes to push the atom out of one lattice site and into another vacant lattice site [16]. The force on the migrating atom due to $H_{\rm V\,IB}$ in the migration direction was set to zero and the negative of this force was evenly distributed among the rest of the atom s

so that the force on the center of m ass was zero. The position of the m igrating atom was then incremented in the m igration direction. Forces on the the atom in the plane perpendicular to the m igration direction were not articially constrained so that the path the m igrating atom took did not lie on a direct line between the initial position of the atom and the vacancy site. G_m was determined by summing the di erence in $H_{V\,IB}$ before and after incrementing the position of the m igrating atom with the other atom ic positions held xed. We found that the barriers to m igration for ions that do not have a vacancy as a nearest neighbor were lower than for ones who do. Thus the value of Z_m is 8 in M gO.

M D was perform ed using a tim estep of 1 fs w ith a 5th order G ear predictor-corrector schem e [17] in an isobaric-isotherm al ensemble generated using the extended system m ethod [18] for 10 ps equilibration tim es follow ed by a 10 (15) ps switching tim e for the form ation (m igration) energy. Convergence w ith respect to our nom inal 216 atom system size was veri ed for systems w ith up to 1000 atoms to be w ithin 1%. Doubling the integration time resulted in free energy variations of 1% while halving it increased the calculated free energy change by 10%. The computationally e cient rst principles m ethod used here lends itself to dem anding convergence tests, especially w ith respect to system size, that would prove too time-consum ing w ith self-consistent m ethods [5].

Values of G_{f} for bound pairs and G_{m} are given in Table I. At 0 GPa, these energies are within 5% of those derived from previous theoretical and experim ental results [3,4,6]. To determ ine the dom inant vacancy mechanism, we calculated the binding energy G_b of a bound pair from the di erence in Gf between bound vacancy pairs and those with the largest possible distance between vacant Mg and O sites in a 1000 atom supercell corrected for in age forces [20] and found $\,$ G $_{
m b}$ = 2.5 10 19 J at 0 G P a and 2000 K and 7.0 10 19 J at 140 GPa and 3000 K.No signi cant changes in m igration energy relative to the bound pair simulation were found. Assuming that the variation in binding energy is linear in pressure and independent of tem perature and taking into account the con gurational entropy, we calculated the vacancy concentration and G ibbs free energy change for crystals containing bound and disassociated pairs relative to the perfect crystal [2]. This analysis shows that Schottky defects dom inate at 1000 K or above due to entropy contributions (low er tem peratures will favor the bound state). Ionic conductivity measurements indicate that M g di usion $(D_{M g})$ is controlled by impurities [19] whereas 0 di usion (D_0) is intrinsic in nature and directly com parable to our analysis. We nd that our predicted D₀ agrees with experiment within mutual error (Fig.1).

Fitting our di usion constants with the relation

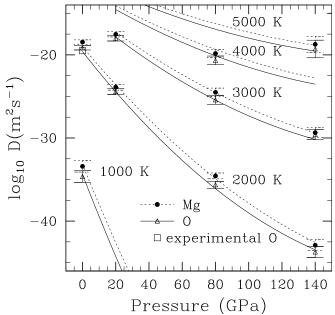


FIG.1. Predicted pressure and temperature dependence of the self-di usion coe cients in M gO.Curves represent the best t to the coe cients using the activation energy-volum e relation given by Equation 7. Vertical sym bol size of experim ental datum taken from R ef. [4] represents uncertainty.

$$\ln D = \ln (a^{2}) + S_{\circ} + P S_{\circ}^{0}$$

$$(E_{\circ} + P V_{\circ} + P^{2} V_{\circ}^{0}) = k_{b} T$$
(7)

gives the zero pressure activation entropy $S_{\circ} = 3-(4)k_b$, its pressure derivative $S_{\circ}^{0} = 0.03-(0.02)k_b$, activation energy $E_{\circ} = 9.0-(9.4) = 10^{-19}$ J, activation volume $V_{\circ} = 16.0-(16.7)$ A³, and its pressure derivative $V_{\circ}^{0} = -0.031-(-0.038)$ A³/GPa for Mg-(0). The activation volume varies as a function of pressure consistant with previous discussions [20{22]. The activation entropy is of the same order as previous estimates of the formation entropy at 0 GPa but varies much less drastically with pressure than a previous estimate [20].

F inally, we considered the hom ologous tem perature relation

$$D = D_{o} \exp (gT_{m} = T)$$
 (8)

com m only used to m odel the dependence of di usion on P and T [23]. Because of the similarity of behavior in di usion of M g and O, we used the e ective di usion coe cient, $D_{eff} = 2D_{Mg}D_{O} = (D_{Mg} + D_{O})$ for D [24]. We tested this m odel using the theoretical melting curve of C ohen and W eitz [25] obtained with the same V IB potential as used here, and the extrapolated experimental melting curve of Zerr and Boehler [26] which has a lower dP = dT. G ood global ts were found using the theoretical melting curve is not consistent with the present di usion results. As discussed in R ef. [25] the experimental results may be in-uenced by Ar solubility in M gO melt at high pressures.

 ${\tt TABLE}\ {\tt I.}$ Free Energies of Form ation and M igration and C ell P aram eter

P	Т	(10 ^{G f} ₁₉ J)		а	Gm			
(G P a)	(K)			(A)	(10 ¹⁹ J)			
					Мg		0	
0	1000	8.19	0.39	4.2495	3.36	0.10	3.75	0.11
0	2000	7.88	0.23	4.3073	2.72	0.12	3.16	0.12
20	2000	12.04	0.40	4.1312	3.75	0.10	4.09	0.10
20	3000	11.57	0.56	4.1687	3.60	0.10	4.06	0.12
80	2000	21.20	0.60	3.8610	5.16	0.10	5.84	0.17
80	3000	21.01	0.90	3.8803	4.99	0.11	5.86	0.07
80	4000	20.75	0.71	3.9031	4.55	0.10	5.61	0.16
140	2000	26.96	0.82	3.7071	6.39	0.10	6.91	0.10
140	3000	25.29	1.11	3.7210	5.99	0.15	6.21	0.21
140	5000	23.44	1.76	3.7509	4.80	0.30	5.69	0.41

Theoretical estimates of the melting curve are generally consistent with each other and with expected therm odynamic parameters.

We also tested the use of zero pressure di usion results only in Eq.8 and found that extrapolations to high pressure using the melting curve were reasonably reliable although some accuracy was lost compared to the results from direct high pressure simulations. This gives justi cation for use of melting curves in estimating high P and T di usion in oxides. In addition, we found that g was less than 14 while the average value for alkali halides is 24 [27] indicating that conclusions based on a system atic value for this parameter may be invalid.

In sum mary, we found (1) excellent agreement with experimental results, (2) that defects are formed from Schottky pairs as opposed to neutral divacancies, and (3) the hom obgoustem perature relation holds within our theoretical framework. These results will help constrain rheological properties of the deep E arth and provide constraints for pressure elects on kinetics in oxides.

ACKNOW LEDGMENTS

We thank W P. Reinhardt and V. Heine for helpful discussions. This work was supported by NSF grant EAR 94-18934. Computations were performed on the Cray J916/12-1024 at the Geophysical Laboratory, CIW, purchased with support from NSF grant EAR 95-12627.

- [1] S.Karato, P.Li, Science, 255, 1238 (1992)
- [2] R J.D. T illey, D effect crystal chem istry and its applications (B lackie, G lasgow and London, 1987)
- [3] K.Ando, in Rheology of Solids and of the Earth, edited by S.Karato and M. Torium i(Oxford Univ. Press, Oxford, 1989)
- [4] M H. Yang and C P. Flynn, Phys. Rev. Let., 73, 1809 (1994)

- [5] A. De Vita, M J. Gillan, J.S. Lin, M C. Payne, I. Stich and L J. Clarke, Phys. Rev. B, 46, 12964 (1992)
- [6] L.Vocadlo, A.W all, S.C. Parker, and G.D. Price, Phys. Earth Planet. Int., 88, 193 (1995)
- [7] W C.Mackrodt and R F.Stewart, J.Phys.C, 12, 5015 (1979)
- [8] I. Inbar and R E. Cohen, Geophys. Res. Let., 22, 1533 (1995)
- [9] R.G.Gordon, and Y.S.Kim, J.Chem. Phys., 56, 3122 (1972)
- [10] R E. Cohen, L L. Boyer, and M J. Mehl, Phys. Rev. B, 35, 5749 (1987)
- [11] L.Hedin and B.I.Lundqvist, J.Phys.C, 4, 2064 (1971)
- [12] M J. M ehl, R E. C ohen and H. K rakauer, J. G eophys. Res., 93, 8009 (1988)
- [13] L L. Boyer, M J. Mehl, J L. Feldman, J R. Hardy, J W. Flocken, and C Y. Fong, Phys. Rev. Lett., 54, 1940 (1985)
- [14] JE.Hunter, W P.Reinhardt, and TF.Davis, J.Chem. Phys., 99, 6856 (1993)
- [15] M. de Koning and A. Antonelli, Phys. Rev. E, 53, 465 (1996)
- [16] V.M ilm an, M C. Payne, V. Heine, R J. Needs, J.S. Lin, and M H. Lee, Phys. Rev. Lett., 70, 2928 (1993)
- [17] C W . G ear, N um erical and initial value problem s in ordinary di erential equations (P rentice H all, Englew ood C li s, N J, 1971)
- [18] G J. Martyna, D J. Tobias and M L. K lien, J. Phys. Chem., 101, 4177 (1994)
- [19] D R. Sem polinski and W D. Kingery, J. Amer. Ceram. Soc., 63, 664 (1980)
- [20] D R.M ills, S.C. Parker and A.W all, Phil.M ag. A, 64, 1133 (1991)
- [21] S.Karato, Phys. Earth Planet. Inter., 24, 1 (1981)
- [22] J.P. Poirier and R.C. Lieberm ann, Phys. Earth Planet. Inter., 35, 283 (1984)
- [23] C G. Sam m is, J.C. Sm ith and G. Schubert, J.G eophys. Res., 86, 10707 (1981)
- [24] J.P. Poirier, Creep of crystals (Cambridge University Press, Cambridge, UK, 1985)
- [25] R.E. Cohen and J.S. Weitz, in High Pressure-Temperature Research: Properties of Earth and Planetary Materials, edited by M.H.Manghnani and T.Yagi (American Geophysical Union, 1997).
- [26] A. Zerr and R. Boehler, Nature, 371, 506 (1994)
- [27] S.Karato, Phys. Earth Planet. Inter., 25, 38 (1981)